

AMENDMENTS TO THE SPECIFICATIONS ARE AS FOLLOWS:

The 4th paragraph on page 6 of the application is amended as below:

The substrate is then subjected to sequential dual annealing steps. The first step is a low energy multiple-pulse laser anneal in the sub-melt regime. ~~Laser parameters are adjusted so as to prevent the melting of the amorphized silicon layer by ion implantation during irradiation of the surface. Multiple pulse laser annealing in the sub-melt regime of the amorphized silicon layer is adequate to activate the dopants and reduce the junction sheet resistance. Due to short annealing time and the absence of melting of the amorphous silicon layer, there is negligible dopant widening.~~